

IMZ120R060M1HXKSA1-VB Datasheet  
N-Channel 1200V (D-S) SiC Power MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	1200	
R <sub>DS(on)</sub> at 25 °C (Ω)	V <sub>GS</sub> = 18 V	0.080
Q <sub>g</sub> (nC)	108	

**FEATURES**

- Low figure-of-merit (FOM) R<sub>on</sub> x Q<sub>g</sub>
- Low input capacitance (C<sub>iss</sub>)
- Reduced switching and conduction losses
- Ultra low gate charge (Q<sub>g</sub>)
- Avalanche energy rated (UIS)



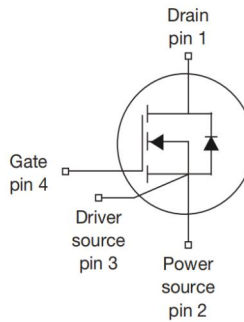
**APPLICATIONS**

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- DC/DC converter

TO-247-4L



- Pin1 D - Drain
- Pin2 S - Source(Power)
- Pin3 S - Source(Driver)
- Pin4 G - Gate



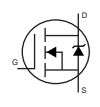
N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	1200	V
Gate-Source Voltage	V <sub>GS</sub>	-10 / +22	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	V <sub>GS</sub> at 18 V	T <sub>C</sub> = 25 °C	A
		T <sub>C</sub> = 100 °C	
Pulsed Drain Current <sup>a</sup>	I <sub>DM</sub>	90	
Linear Derating Factor		2.1	W/°C
Single Pulse Avalanche Energy <sup>b</sup>	E <sub>AS</sub>	1200	mJ
Maximum Power Dissipation	P <sub>D</sub>	320	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Drain-Source Voltage Slope	dV/dt	T <sub>J</sub> = 125 °C	V/ns
Reverse Diode dV/dt <sup>d</sup>		15	
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s	260	°C

**Notes**

- Repetitive rating; pulse width limited by maximum junction temperature.
- V<sub>DD</sub> = 100 V, starting T<sub>J</sub> = 25 °C, L = 30mH, R<sub>g</sub> = 25 Ω, I<sub>AS</sub> = 9A.
- 1.6 mm from case.
- I<sub>SD</sub> ≤ I<sub>D</sub>, dI/dt = 100 A/μs, starting T<sub>J</sub> = 25 °C.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	40	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.47	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	1200	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$	-	0.70	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 10\text{ mA}$	2.5	-	4.5	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = +22\text{ V}$	-	-	100	nA
		$V_{GS} = -10\text{ V}$	-	-	100	$\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$	-	10	-	$\mu\text{A}$
		$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	100	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 18\text{ V}, I_D = 30\text{ A}$	-	0.080	-	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 0\text{ V}, I_D = 30\text{ A}$	-	16	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 800\text{ V}, f = 1\text{ MHz}$	-	2800	-	pF
Output Capacitance	$C_{oss}$		-	123	-	
Reverse Transfer Capacitance	$C_{rss}$		-	10	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 800\text{ V}, V_{GS} = 0\text{ V}$	-	156	-	
Effective Output Capacitance, Time Related <sup>b</sup>	$C_{o(tr)}$		-	268	-	
Total Gate Charge	$Q_g$	$V_{GS} = -5/18\text{ V}, I_D = 20\text{ A}, V_{DS} = 800\text{ V}$	-	108	-	nC
Gate-Source Charge	$Q_{gs}$		-	29	-	
Gate-Drain Charge	$Q_{gd}$		-	33	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 800\text{ V}, I_D = 20\text{ A}, V_{GS} = -5/18\text{ V}, R_g = 2\text{ }\Omega$	-	18	25	ns
Rise Time	$t_r$		-	24	55	
Turn-Off Delay Time	$t_{d(off)}$		-	80	-	
Fall Time	$t_f$		-	12	-	
Gate Input Resistance	$R_g$		$f = 1\text{ MHz}, \text{open drain}$	-	3.2	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	30	A
Pulsed Diode Forward Current	$I_{SM}$		-	-	90	
Diode Forward Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 30\text{ A}, V_{GS} = 0$	-	-	4.1	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 30\text{ A}, di/dt = 1000\text{ A}/\mu\text{s}, V_R = 800\text{ V}$	-	70	-	ns
Reverse Recovery Charge	$Q_{rr}$		-	220	-	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$		-	60	-	A

**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .
- b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

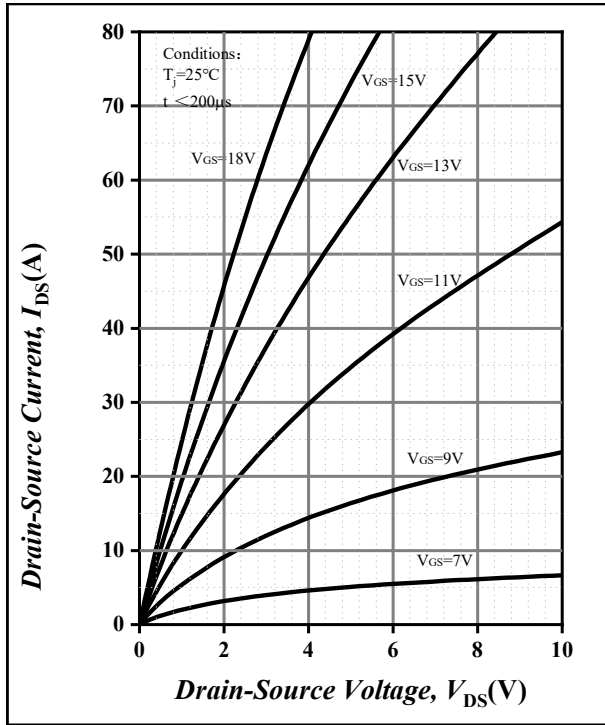


Fig.1 Output characteristics  $T_j=25^\circ\text{C}$

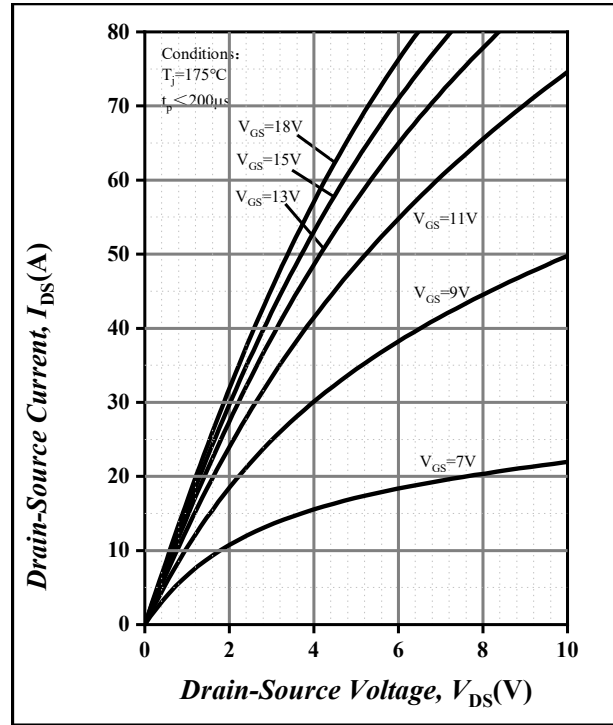


Fig.2 Output characteristics  $T_j=175^\circ\text{C}$

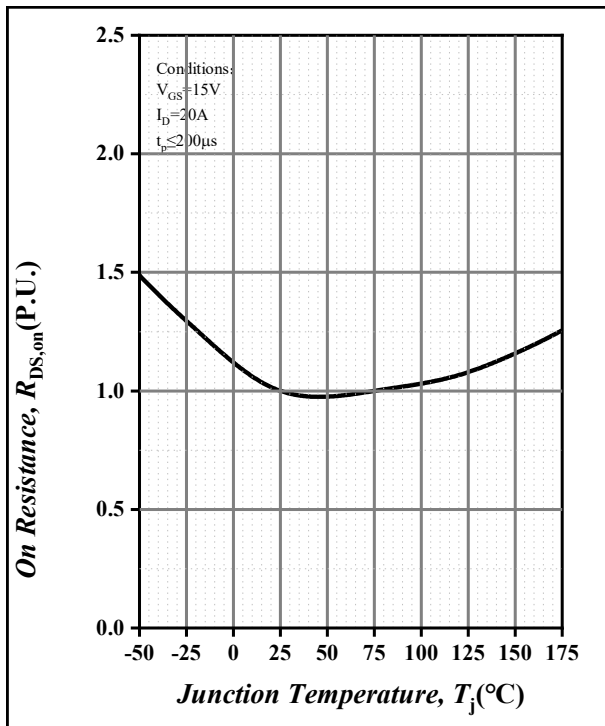


Fig.3 Normalized On-Resistance vs. Temperature

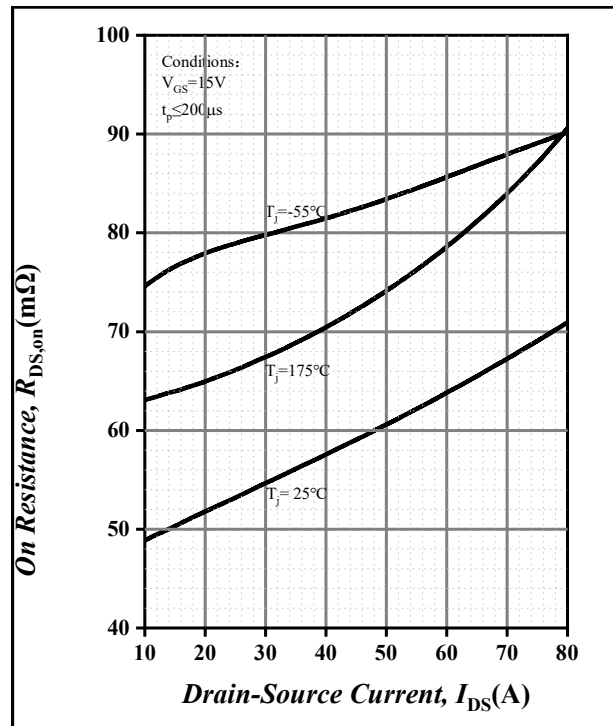


Fig.4 On-Resistance vs. Drain Current For Various Temperatures

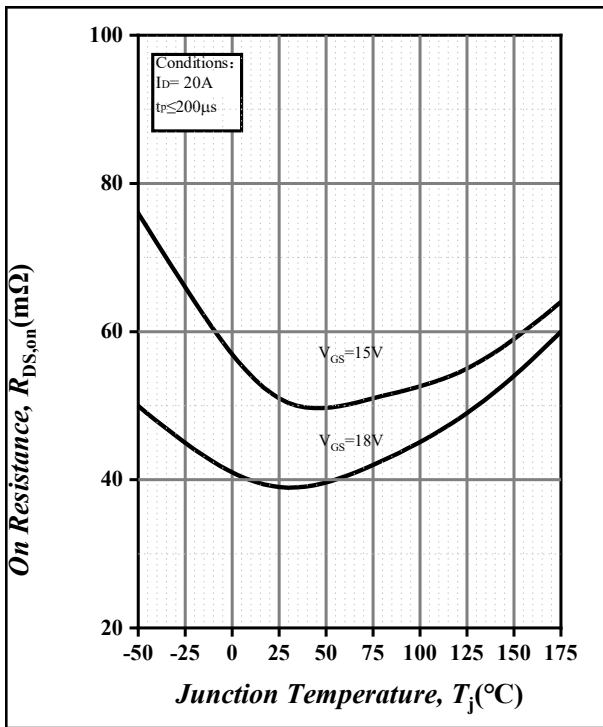


Fig.5 On-Resistance vs. Temperature For Various Gate Voltage

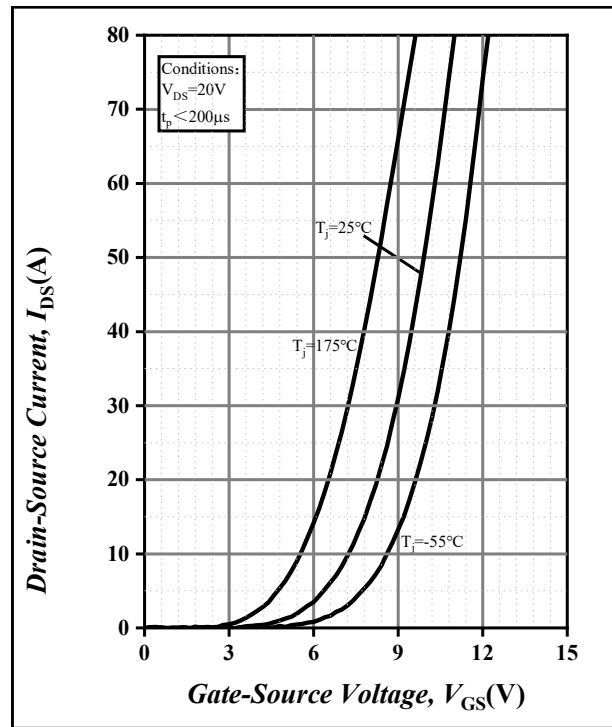


Fig.6 Transfer Characteristic For Various Junction Temperatures

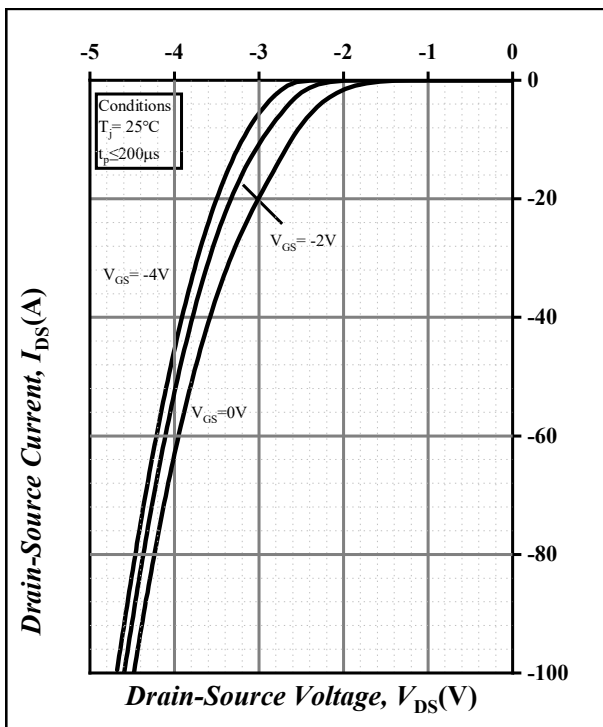


Fig.7 Body Diode Characteristic at 25 $^{\circ}$ C

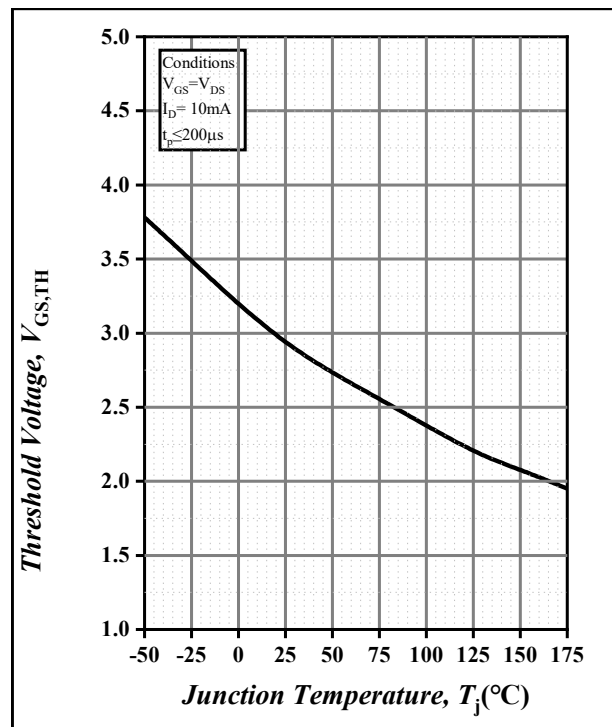


Fig.8 Threshold Voltage vs. Temperature



Fig.9 Gate Charge Characteristics

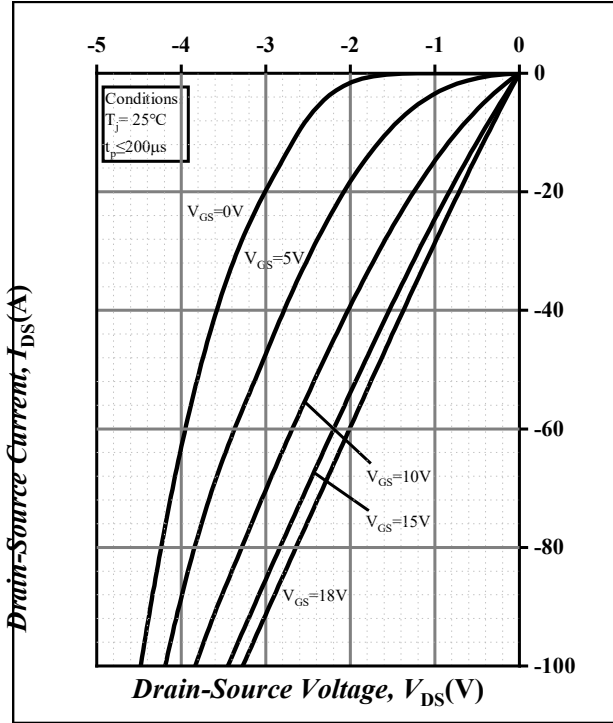


Fig.10 3<sup>rd</sup> Quadrant Characteristic at 25°C

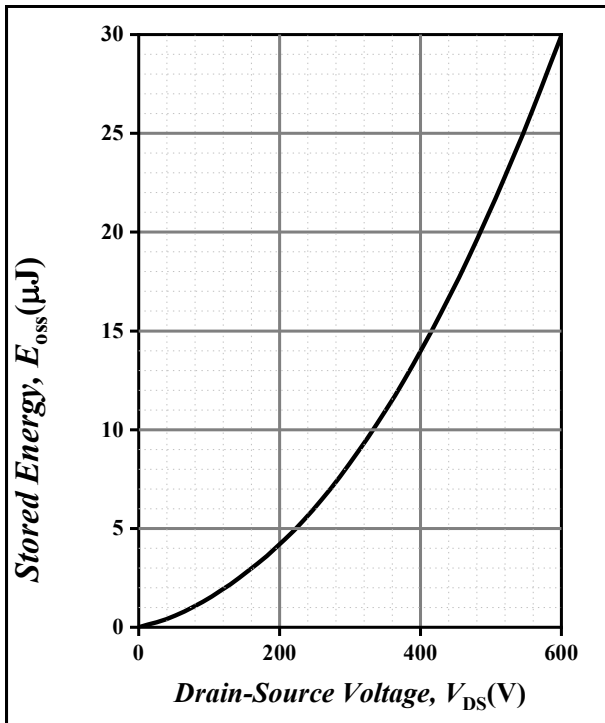


Figure 11. Output Capacitor Stored Energy



Fig.12 Capacitances vs. Drain-Source Voltage(0-200V)

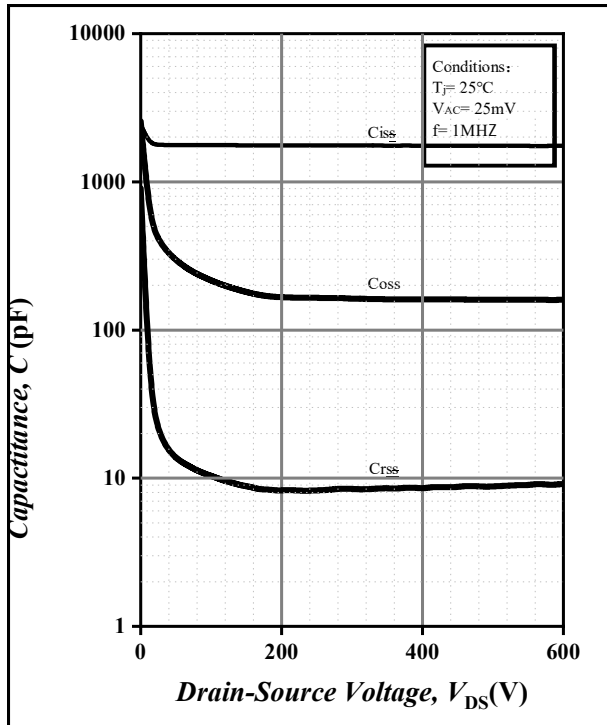


Fig.13 Capacitances vs. Drain-Source Voltage(0-600V)

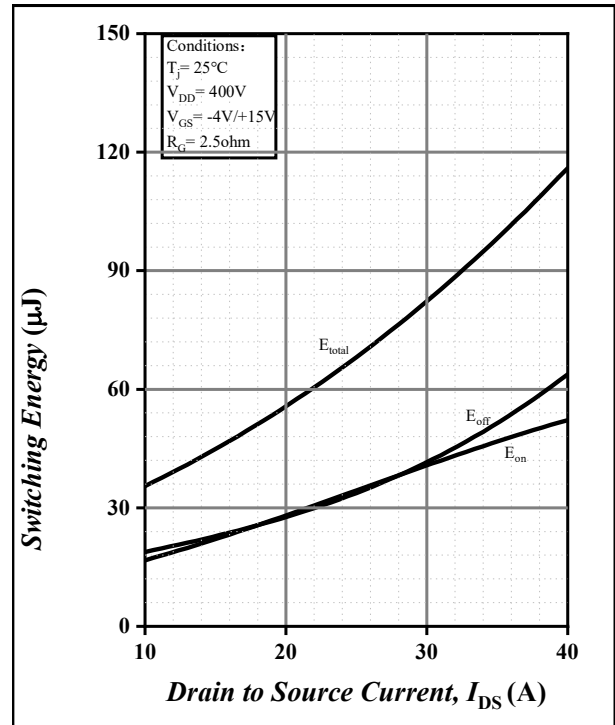


Figure 14. Clamped Inductive Switching Energy vs. Drain Current( $V_{DD}=400V$ )

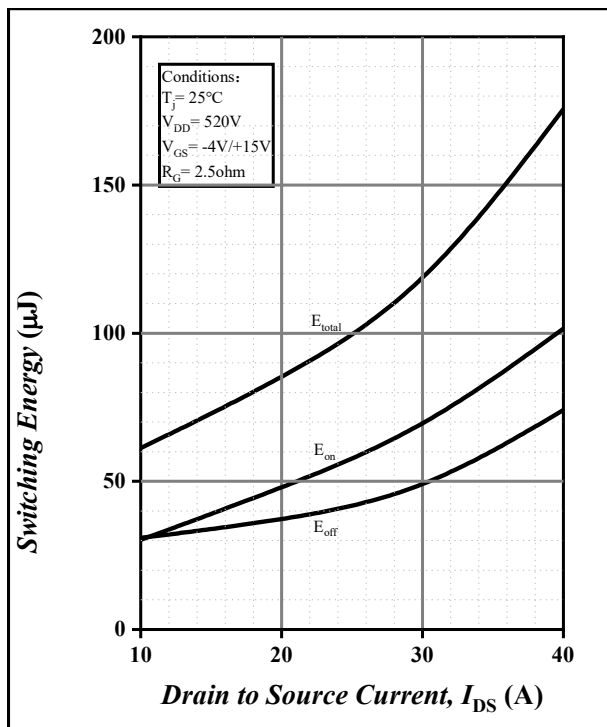


Figure 15. Clamped Inductive Switching Energy vs. Drain Current( $V_{DD}=520V$ )

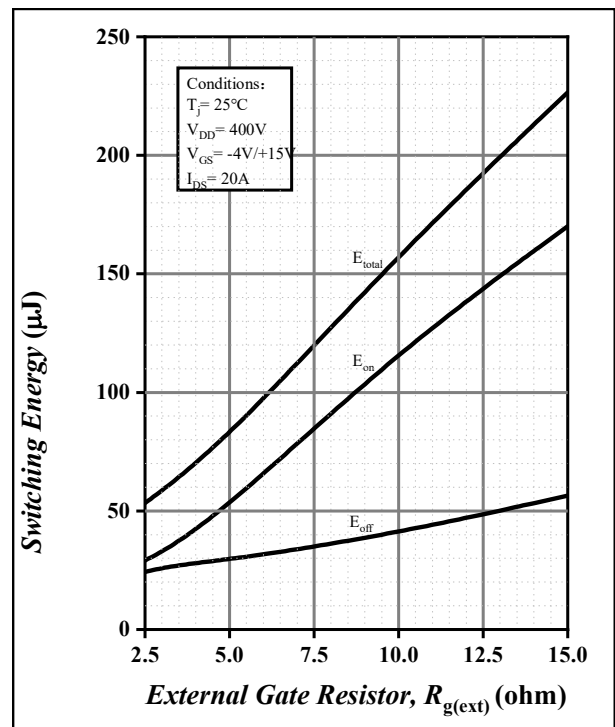


Figure 16. Clamped Inductive Switching Energy vs.  $R_{g(ext)}$

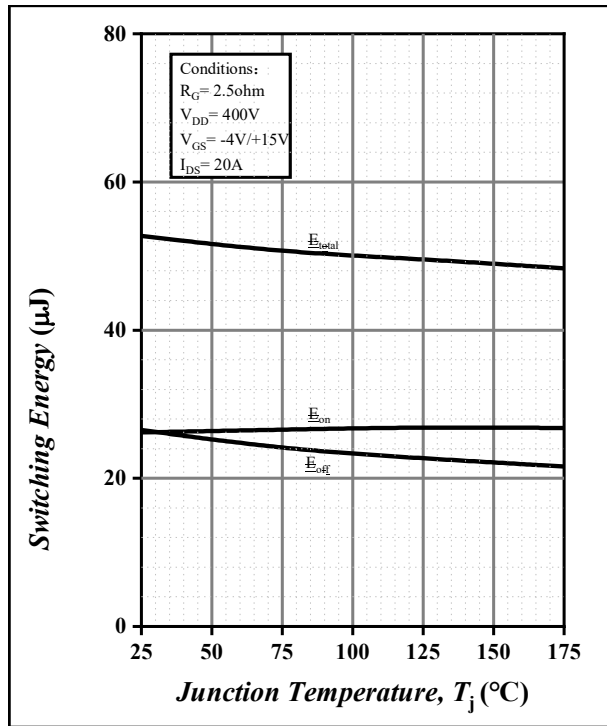


Figure 17. Clamped Inductive Switching Energy vs. Temperature



Figure 18. Switching Times vs.  $R_{g(ext)}$



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